

P-Channel Enhancement Mode Power MOSFET SOT-23

Product Summary

- $V_{DS} = -40V, I_D = -3A$
- $R_{DS(on)} < 138m\Omega @ V_{GS} = -10V$
- $R_{DS(on)} < 175m\Omega @ V_{GS} = -4.5V$

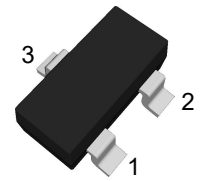
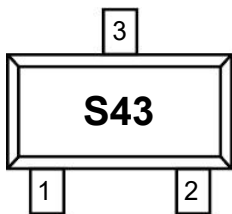
Features

- Advanced Trench Technology
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 1

Application

- Load Switch
- PWM Application
- Power Management

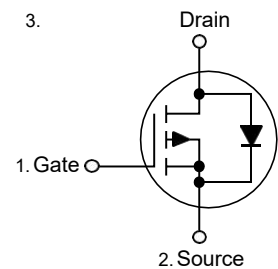
Marking Code



(Top View)

Pin	Description
1	Gate
2	Source
3	Drain

Schematic Diagram



Absolute Maximum Ratings

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	$-I_D$	3	A
Drain Current-Pulsed ^{Note1}	$-I_{DM}$	12	A
Maximum Power Dissipation	P_D	0.7	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	179	°C/W
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3URG8XWPDU\

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)HDWXUHV

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Moisture Sensitivity Level 1

\$SSOLF DWLRQ

Load Switch
PWM Application
Power Management

0DUNL&RGH

3

6

1

2

627

3

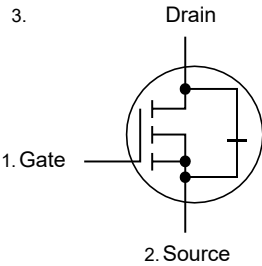
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7R9LHZ

3LQ	'HVFULSV
1	Gate
2	Source
3	Drain

6FKHPD'WDFUDP



\$EVROXWHPX5PDWLQJV

(Ta=25 / unless otherwise specified)

3DUDPHWHU	6\PERO	9DOXH	8QLW
Drain-Source Voltage	$-V_{DS}$	40	V
Gate-Source Voltage	V_{GS}	± 20	V
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7KHUR&KODUFWHULVWL FV

Thermal Resistance,Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	179	$^{\circ}C/W$
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3URG~~X~~~~F~~WPDU\

6 2 7

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) H D W X U H V

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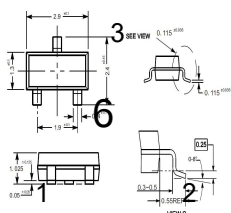
\$SSOLF DWLRQ

z Load Switch

z PWM Application

- z Power Management

0 D U N L & O R J G H

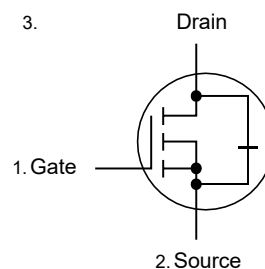


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7R9LHZ

3 L Q	' H V F U L S V
1	Gate
2	Source
3	Drain

6 F K H P D' ~~W D J~~ F U D P



\$ E V R O O K D W H P X 5 P D W L Q J V

(Ta=25 / unless otherwise specified)

3 D U D P H W H U	6 \ P E R O	9 D O X H	8 Q L W
Drain-Source Voltage	-V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	-I _D	3	A
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7KHUR&KODUDFWHULVWL FV

Thermal Resistance, Junction-to-Ambient ^{Note2}	R _{θJA}	179	°C/W
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3 U R G 6 7 W P D U \

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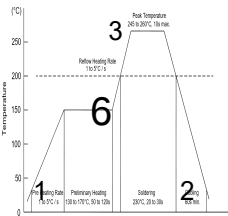
) H D W X U H V

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\$ S S O L F D W L R Q

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0 D U N 6 7 Q J G H



6 2 7

3

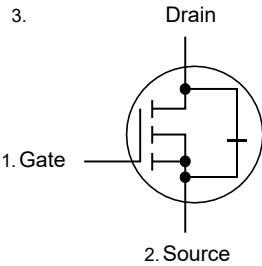
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7 R 9 L H Z

3 L Q	' H V F U L S V
1	Gate
2	Source
3	Drain

6 F K H P D ' W D J F U D P



\$ E V R O O D W H P X 5 P D W L Q J V

(Ta=25 / unless otherwise specified)

3 D U D P H W H U	6 \ P E R O	9 D O X H	8 Q L W
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7 K H U R 6 7 Q J G H U D F W H U L V W L F V

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	179	°C/W
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